

SOT223 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTORS

BF721 BF723

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FEATURES

- * High breakdown and low saturation voltages

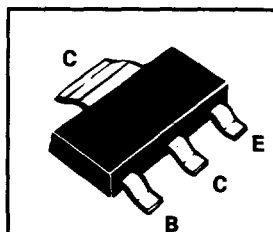
APPLICATIONS

- * Suitable for video output stages in TV sets
- * Switching power supplies

COMPLEMENTARY TYPES:- BF721 - BF720 BF723 - BF722

PARTMARKING DETAILS:- Device Type in Full

ABSOLUTE MAXIMUM RATINGS.



PARAMETER	SYMBOL	BF721	BF723	UNIT
Collector-Base Voltage	V_{CBO}	-300	-250	V
Collector-Emitter Voltage	V_{CEO}	-300	-250	V
Emitter-Base Voltage	V_{EBO}		-5	V
Peak Pulse Current	I_{CM}		-100	mA
Continuous Collector Current	I_C		-50	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}		-2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$		-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300 -250			V	$I_C = -10\mu A, I_E = 0$ $I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300 -250			V	$I_C = -1mA, I_B = 0^*$ $I_C = -1mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}			-10	nA	$V_{CB} = -200V, I_E = 0$ †
Collector Cut-Off Current	I_{CER}			-50 -10	nA μA	$V_{CE} = -200V, R_{BE} = 2.7K\Omega$ $V_{CE} = -200V, R_{BE} = 2.7K\Omega$ †
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{EB} = -5V, I_C = 0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.6	V	$I_C = -30mA, I_B = -5mA^*$
Base Emitter Saturation Voltage	$V_{BE(sat)}$			-0.9	V	$I_C = -20mA, I_B = -2mA^*$
Static Forward Current Transfer Ratio	h_{FE}	-50				$I_C = -25mA, V_{CE} = -20V^*$
Transition Frequency	f_T		100		MHz	$I_C = -10mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	C_{obo}		0.8		pF	$V_{CB} = -30V, f = 1MHz$

† $T_{amb} = 150^{\circ}C$

* Measured under pulsed conditions. Pulse width = 300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FMMTA92 datasheet.